

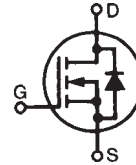
## HiPerFET™ Power MOSFETs

**IXFA 3N120**  
**IXFP 3N120**

**V<sub>DSS</sub> = 1200 V**  
**I<sub>D25</sub> = 3 A**  
**R<sub>DS(on)</sub> = 4.5 Ω**

N-Channel Enhancement Mode  
Avalanche Rated, Low Q<sub>g</sub>, High dv/dt

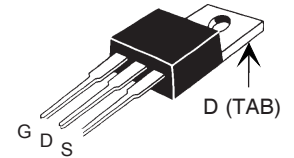
Preliminary Data Sheet



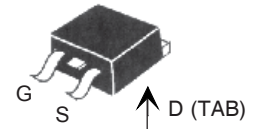
**t<sub>rr</sub> ≤ 300 ns**

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	1200	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GS</sub> = 1 MΩ	1200	V
V <sub>GS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	3	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	12	A
I <sub>AR</sub>	T <sub>C</sub> = 25°C	3	A
E <sub>AR</sub>	T <sub>C</sub> = 25°C	20	mJ
E <sub>AS</sub>		700	mJ
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> ; di/dt ≤ 100 A/μs, V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C, R <sub>G</sub> = 4.7 Ω	10	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	200	W
T <sub>J</sub>		-55 to +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 to +150	°C
T <sub>L</sub>	1.6 mm (0.063 in) from case for 10 s	300	°C
M <sub>d</sub>	Mounting torque (TO-220)	1.13/10	Nm/lb.in.
Weight	TO-220	4	g
	TO-263	2	g

TO-220 (IXFP)



TO-263 (IXFA)



G = Gate      D = Drain  
S = Source    TAB = Drain

### Features

- Low gate charge and capacitances
  - easier to drive
  - faster switching
- International standard packages
- Low R<sub>DS(on)</sub>
- Rated for unclamped Inductive load Switching (UIS)
- Molding epoxies meet UL 94 V-0 flammability classification

### Advantages

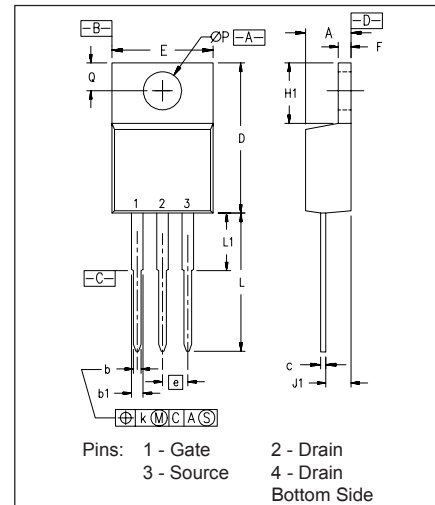
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA	1200		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.5 mA	2.5		V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V <sub>DC</sub> , V <sub>DS</sub> = 0			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0 V		T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	50 μA 2 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 I <sub>D25</sub> Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			4.5 Ω

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
g <sub>fs</sub>	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 0.5 • I <sub>D25</sub> , pulse test	1.5	2.5	S
C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		1050	pF
C <sub>oss</sub>			100	pF
C <sub>rss</sub>			25	pF
t <sub>d(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub> R <sub>G</sub> = 4.7 Ω (External)		17	ns
t <sub>r</sub>			15	ns
t <sub>d(off)</sub>			32	ns
t <sub>f</sub>			18	ns
Q <sub>g(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub>		39	nC
Q <sub>gs</sub>			9	nC
Q <sub>gd</sub>			22	nC
R <sub>thJC</sub>	(TO-220)			0.62 KW
R <sub>thCK</sub>			0.25	KW

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
I <sub>S</sub>	V <sub>GS</sub> = 0 V			3 A
I <sub>SM</sub>	Repetitive; pulse width limited by T <sub>JM</sub>			12 A
V <sub>SD</sub>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t <sub>rr</sub>	I <sub>F</sub> = I <sub>S</sub> , -di/dt = 100 A/μs, V <sub>R</sub> = 100 V			300 ns
Q <sub>RM</sub>			0.4	μC
I <sub>RM</sub>			1.2	A

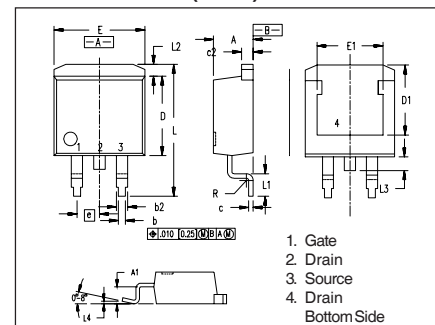
### TO-220 (IXFP) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-220 AB.

### TO-263 (IXFA) Outline

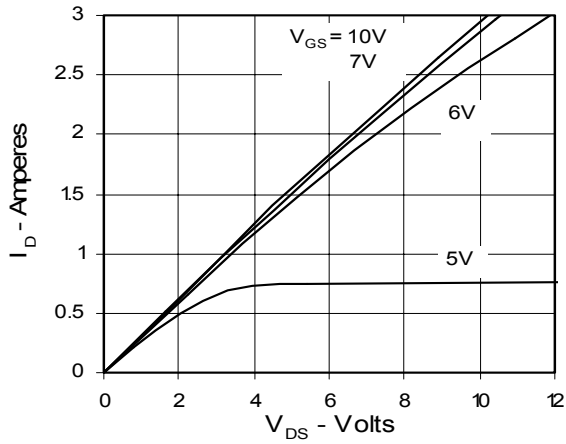


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

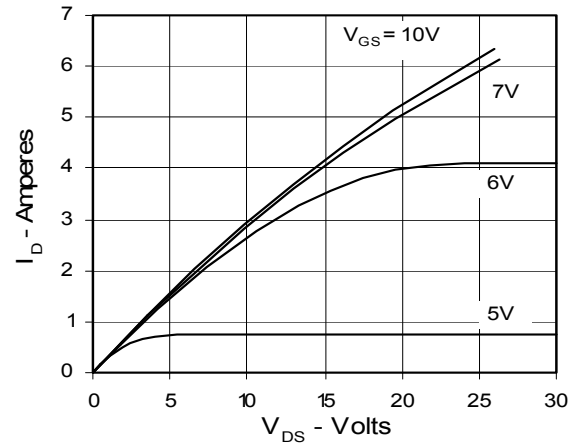
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,710,463
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505		

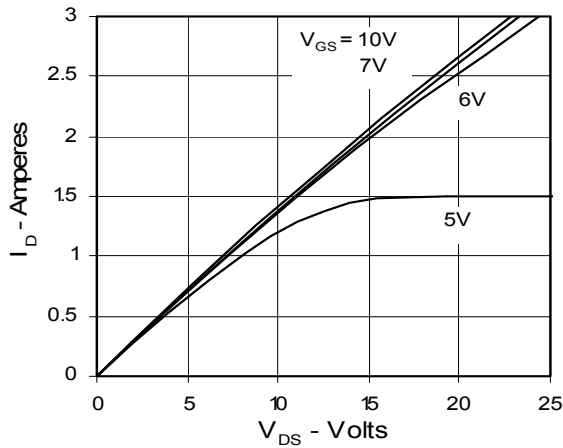
**Fig. 1. Output Characteristics**  
@ 25 Deg. C



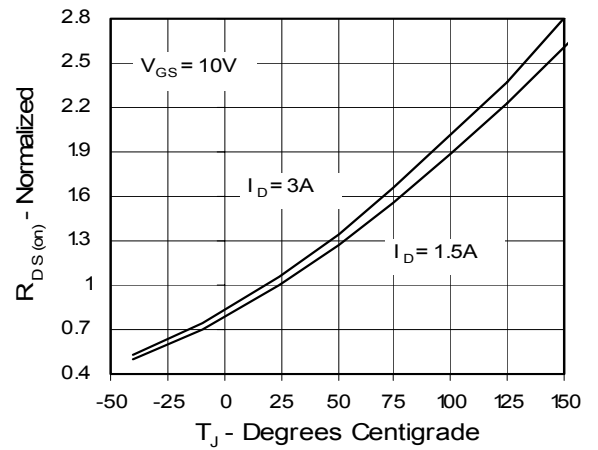
**Fig. 2. Extended Output Characteristics**  
@ 25 deg. C



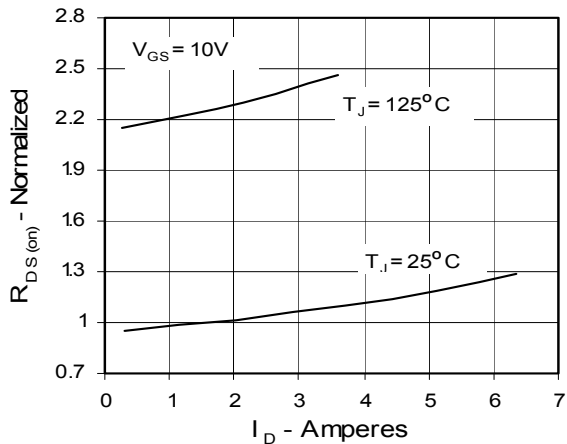
**Fig. 3. Output Characteristics**  
@ 125 Deg. C



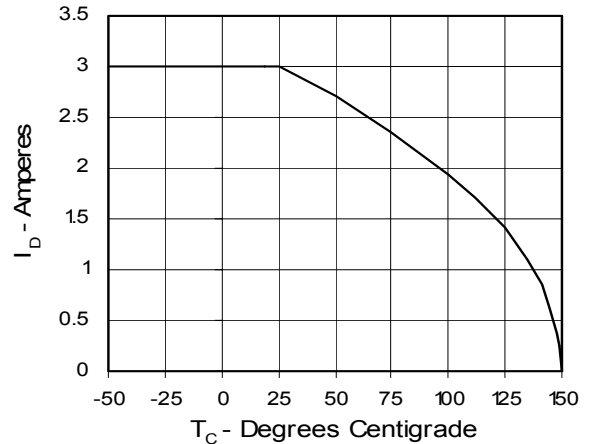
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs. Junction Temperature**



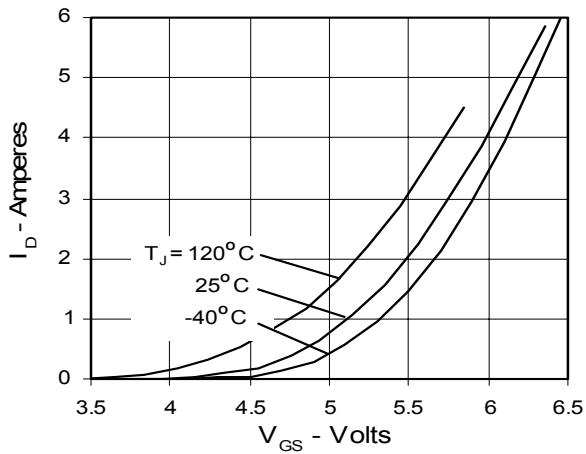
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs.  $I_D$**



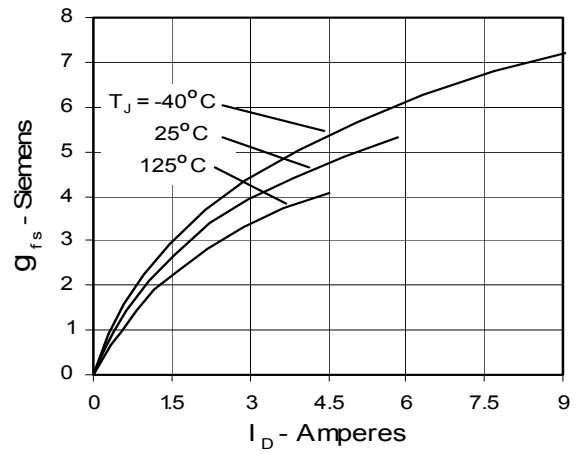
**Fig. 6. Drain Current vs. Case Temperature**



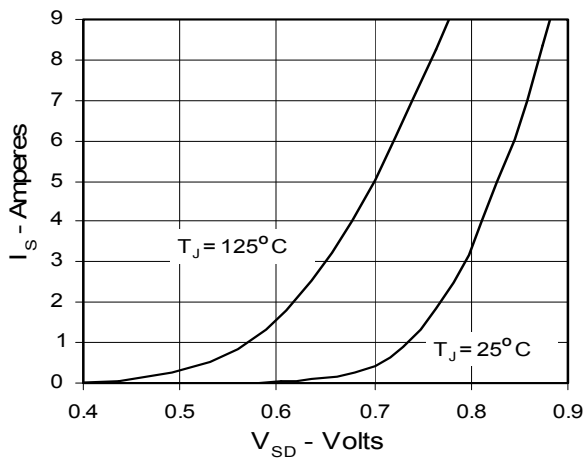
**Fig. 7. Input Admittance**



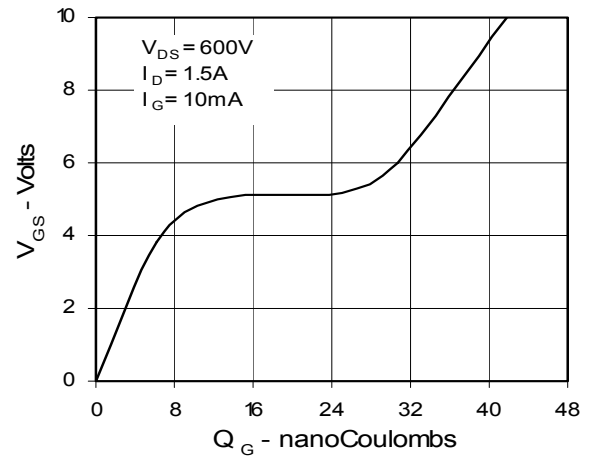
**Fig. 8. Transconductance**



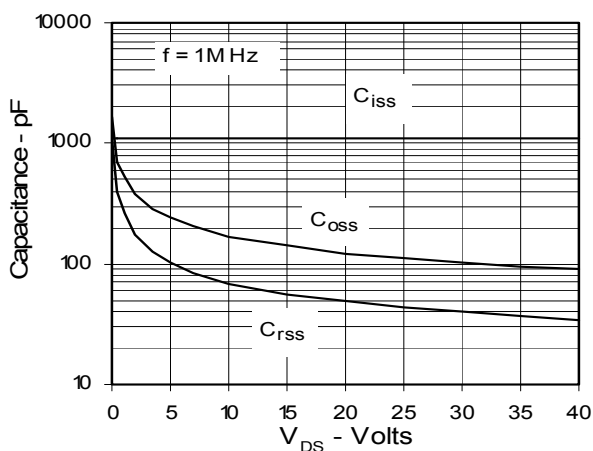
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**

